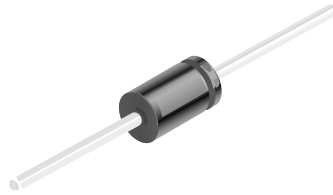


# FDH444



**DO-35**

Color Band Denotes Cathode

## Small Signal Diode

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{RRM}$	Maximum Repetitive Reverse Voltage	150	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 4.0	A A
$T_{stg}$	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	175	$^\circ\text{C}$

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	$^\circ\text{C}/\text{W}$

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
$V_R$	Breakdown Voltage	$I_R = 100 \mu\text{A}$	150		V
$V_F$	Forward Voltage	$I_F = 200 \text{ mA}$ $I_F = 300 \text{ mA}$		1.1 1.2	V V
$I_R$	Reverse Current	$V_R = 100 \text{ V}$ $V_R = 100 \text{ V}, T_A = 150^\circ\text{C}$		50 100	nA $\mu\text{A}$
$C_T$	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.5	pF
$t_{rr}$	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}$ , $R_L = 100 \Omega, I_{rr} = 3.0 \text{ mA}$		60	ns